

### General Description

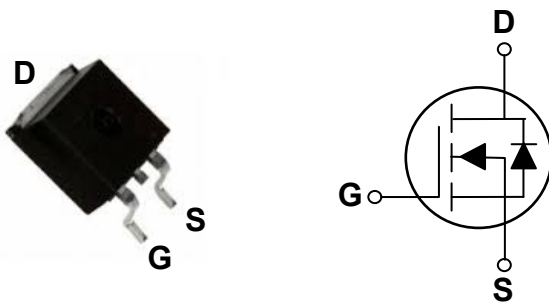
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	3mΩ	176A

### Features

- 30V, 176A,  $R_{DS(ON)} = 3m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### TO263 Pin Configuration



### Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2<sup>nd</sup> SR



### Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	176	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	111	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	704	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	180	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	60	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	168	W
	Power Dissipation – Derate above $25^\circ\text{C}$	1.34	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.74	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.03	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>3</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	2.4	3	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	3.2	4	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	---	16	---	S

**Dynamic Characteristics**

Q <sub>g</sub>	Total Gate Charge <sup>3,4</sup>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =24A	---	40	75	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3,4</sup>		---	6	12	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3,4</sup>		---	19	35	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3,4</sup>	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =1Ω I <sub>D</sub> =1A	---	20	40	ns
T <sub>r</sub>	Rise Time <sup>3,4</sup>		---	32	60	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3,4</sup>		---	75	130	
T <sub>f</sub>	Fall Time <sup>3,4</sup>		---	28	55	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	4800	8000	pF
C <sub>oss</sub>	Output Capacitance		---	735	1300	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	420	800	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	1.6	3.5	Ω

**Drain-Source Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	176	A
I <sub>SM</sub>	Pulsed Source Current <sup>3</sup>		---	---	352	A
V <sub>SD</sub>	Diode Forward Voltage <sup>3</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>DS</sub> =30V, I <sub>S</sub> =1A, di/dt=100A/μs	---	49	85	ns
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	18	35	nC

**Note :**

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=60A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

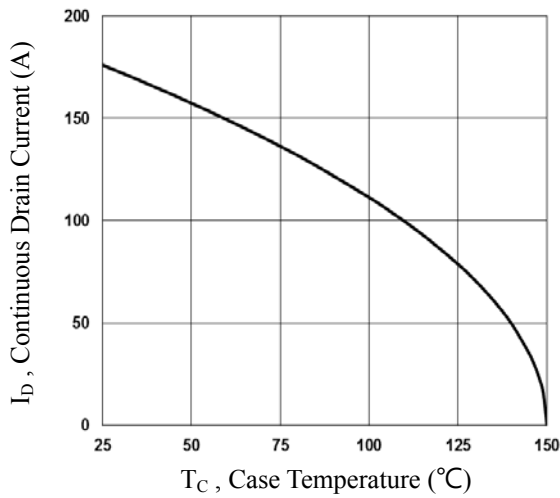


Fig.1 Continuous Drain Current vs.  $T_C$

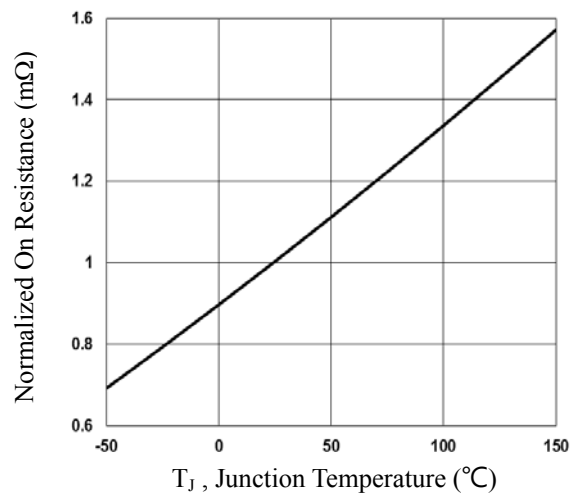


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$

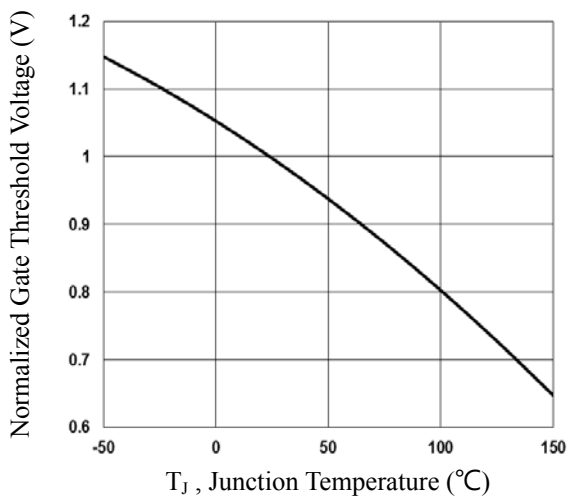


Fig.3 Normalized  $V_{th}$  vs.  $T_J$

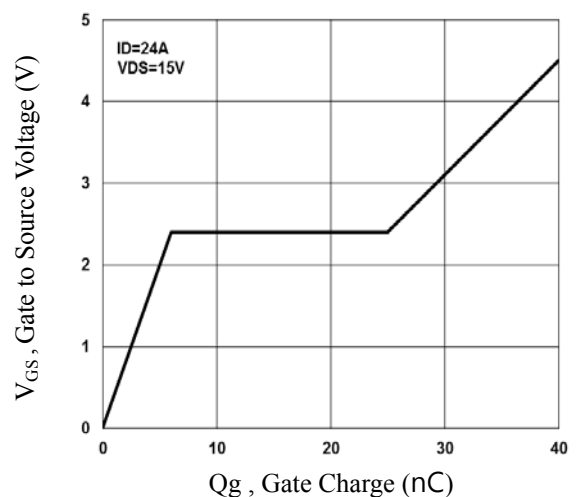


Fig.4 Gate Charge Waveform

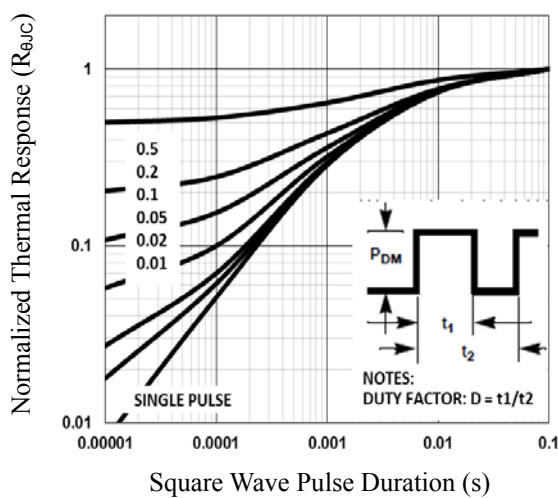


Fig.5 Normalized Transient Impedance

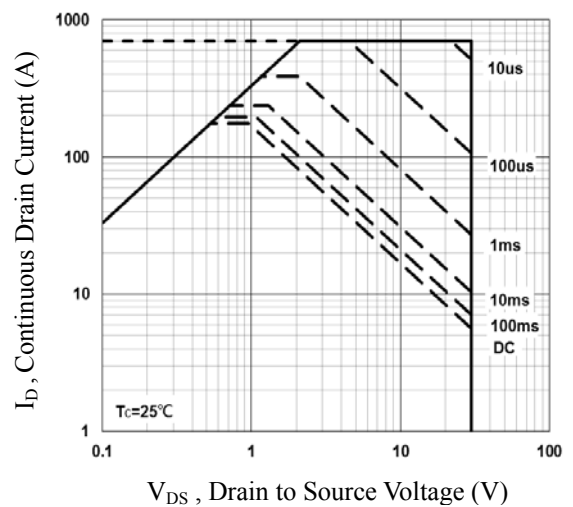


Fig.6 Maximum Safe Operation Area

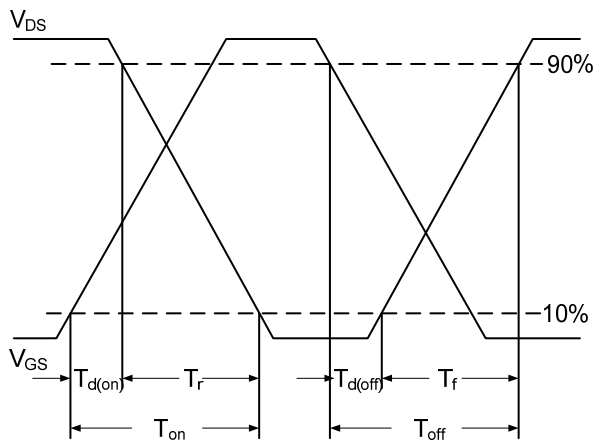


Fig.7 Switching Time Waveform

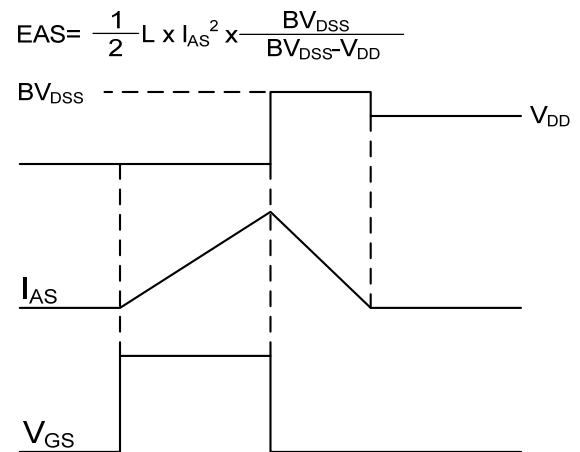


Fig.8 EAS Waveform